

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (Currently Amended) A transistor structure, comprising:
a single gate electrode formed of silicided polysilicon,
a gate signal line, and
a plurality of conductive plugs formed of a periodic table column IVB, VB, VIB, and/or VIIB metal, each of the plurality of conductive plugs electrically interconnecting the single gate electrode in a distributed manner across a length of the single gate electrode and the gate signal line,
wherein the single gate electrode, the conductive plug, and the gate signal line are arranged vertically with respect to a substrate upon which the transistor structure is mounted.
2. (Original) The transistor structure of Claim 1, wherein the conductive plug is formed of two or more layers.
3. (Original) The transistor structure of Claim 2, wherein each of the two or more layers is formed of a different material.
4. (Previously Presented) The transistor structure of Claim 1, wherein the conductive plug has a rectangular cross section.
5. (Original) The transistor structure of Claim 4, wherein the conductive plug has a width between 120 nm and 400 nm, inclusive, a length between 120 nm and 400 nm,

inclusive, and a height between 200 nm to 500 nm.

6. (Original) The transistor structure of Claim 5, wherein the conductive plug has a width of 160 nm, a length of 160 nm, and a height of 280 nm.

7. (Original) The transistor structure of Claim 1, where in the gate electrode has a generally rectangular shape.

8. (Original) The transistor structure of Claim 7, wherein the gate electrode has a length between 2 microns and 10 microns, a width between 300 nm and 1 micron, and a thickness between 120 nm and 300 nm.

9. (Original) The transistor structure of Claim 8, wherein the gate electrode has a length of 4.8 microns, a width of 420 nm, and a height of 180 nm.

10. (Original) The transistor structure of Claim 1, wherein the conductive plug is formed of chromium or molybdenum.

11. (Original) The transistor structure of Claim 1, wherein the conductive plug is formed of tungsten.

12. (Original) The transistor structure of Claim 1, wherein the gate signal line is formed of copper.

13. (Original) The transistor structure of Claim 1, wherein the gate signal line is formed of aluminum.

14-27. (Canceled)